

IN THE CLAIMS:

The status of each claim that has been introduced in the above-referenced application is identified in the ensuing listing of the claims. This listing of the claims replaces all previously submitted claims listings.

1. (Currently amended) A semiconductor device structure, comprising:  
a first layer comprising anti-reflective material; and  
a second layer comprising silicon nitride, located over the first layer, and substantially free of in-film particles or surface roughness features of ~~more than~~ about 120 nm to about 150 nm.
2. (Previously presented) The semiconductor device structure of claim 1, wherein the anti-reflective material comprises silicon atoms and nitrogen atoms.
3. (Previously presented) The semiconductor device structure of claim 2, wherein the anti-reflective material further comprises oxygen atoms.
4. (Previously presented) The semiconductor device structure of claim 1, wherein the anti-reflective material comprises  $\text{Si}_x\text{O}_y\text{N}_z$ , where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.
5. (Previously presented) The semiconductor device structure of claim 1, wherein a surface of the first layer is substantially free of at least one of measurable particulates and surface roughness.
6. (Previously presented) The semiconductor device structure of claim 1, wherein the second layer is substantially free of at least one of particles and surface roughness features of at least about 120 nm.

7. (Previously presented) The semiconductor device structure of claim 1, wherein the second layer is formed on the first layer.

8. (Previously presented) A semiconductor device structure, comprising:  
a first layer comprising anti-reflective material; and  
a second layer comprising silicon nitride, located over the first layer, and being substantially free of in-film particles or surface roughness features of at least about 120 nanometers.

9. (Previously presented) The semiconductor device structure of claim 8, wherein the anti-reflective material comprises silicon atoms and nitrogen atoms.

10. (Previously presented) The semiconductor device structure of claim 9, wherein the anti-reflective material further comprises oxygen atoms.

11. (Previously presented) The semiconductor device structure of claim 8, wherein the anti-reflective material comprises  $\text{Si}_x\text{O}_y\text{N}_z$ , where x equals about 0.40 to about 0.65 times the sum of x, y, and z, y equals about 0.02 to about 0.56 times the sum of x, y, and z, and z equals about 0.05 to about 0.33 times the sum of x, y, and z.

12. (Previously presented) The semiconductor device structure of claim 8, wherein a surface of the first layer is substantially free of at least one of measurable particulates and surface roughness.

13. (Canceled)

14. (Previously presented) The semiconductor device structure of claim 8, wherein the second layer is formed on the first layer.